

INTRODUCE:

HVGT high voltage silicon rectifier subassembly is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers

FEATURES:

1. High reliability design.
2. High quality chip.
3. High current . low forward voltage
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Accelerator power supply.
2. High voltage test equipment circuit .
3. General purpose high voltage rectifier.
4. Environmental desulfurization system.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: screw holes.
3. Net weight: 223grams (approx).

SHAPE DISPLAY:

SIZE: (Unit:mm)
HVGT NAME: HVC-243020
HVC-243020 Series

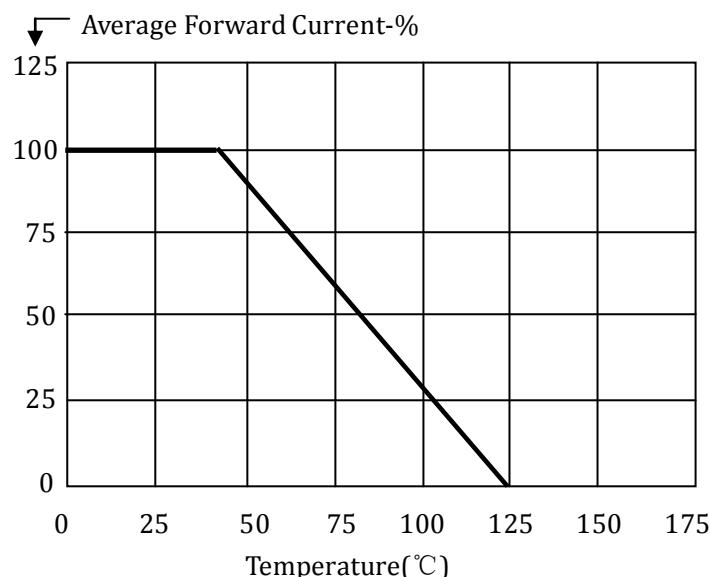
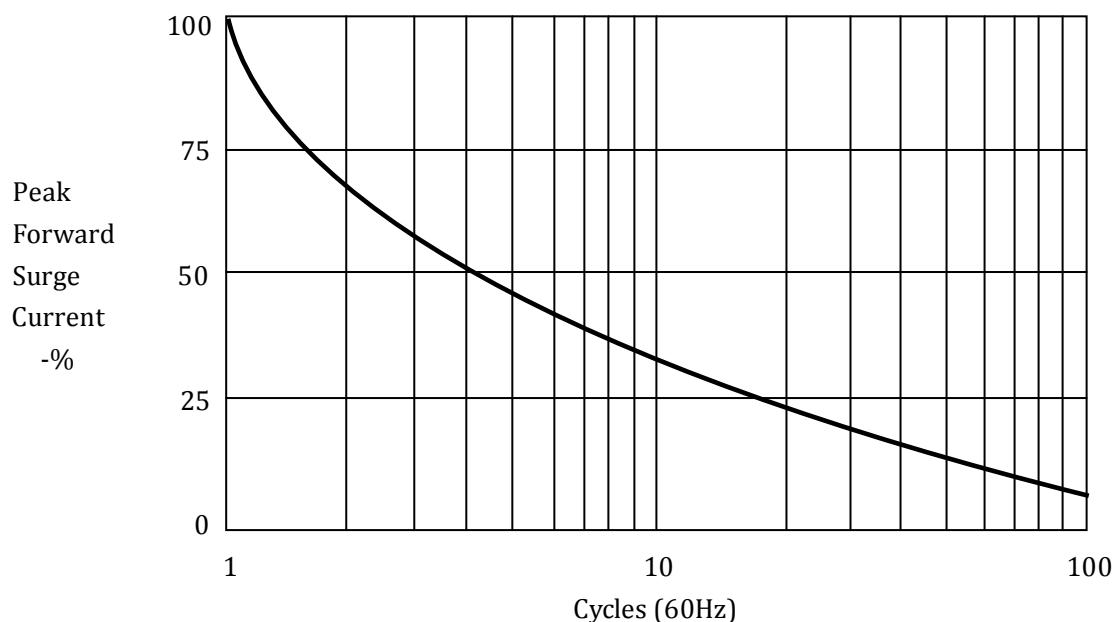
Screw Holes M5


MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V _{RRM}	T _A =25°C	150	kV
Non-Repetitive Peak Reverse Voltage	V _{RSM}	T _A =25°C	180	kV
Average Forward Current Maximum	I _{FAVM}	T _A =40°C	1.0	A
		T _{OIL} =55°C	--	A
Non-Repetitive Forward Surge Current	I _{FSM}	T _A =25°C; 60Hz Half-Sine Wave; 8.3mS	30	A
Junction Temperature	T _J		125	°C
Allowable Operation Case Temperature	T _C		-40~+125	°C
Storage Temperature	T _{STG}		-40~+150	°C

ELECTRICAL CHARACTERISTICS: T_A=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V _{FM}	at 25°C; at I _{FAVM}	216	V
Maximum Reverse Current	I _{R1}	at 25°C; at V _{RRM}	5.0	uA
	I _{R2}	at 100°C; at V _{RRM}	50	uA
Maximum Reverse Recovery Time	T _{RR}	at 25°C; I _F =0.5I _R ; I _R =I _{FAVM} ; I _{RR} =0.25I _R	--	nS
Junction Capacitance	C _J	at 25°C; V _R =0V; f=1MHz	--	pF

Fig 1
Forward Current Derating Curve

Fig 2
Non-Repetitive Surge Current

Marking
Type
Code
Cathode Mark

2CL150KV/1A

 2CL150KV/1A
 HVGT
